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The CID number appears on each page of the manuscript. The complete citation is used on the first page, and an abbreviated version on subsequent pages. Numbers in the index correspond to the last two digits of the six-digit CID number.

Contents

Part One

xvii	Symposium Committee
xix	Conference Committee

SESSION 1 INVITED SESSION

- 6922 02 **Diffractiⁿon order control in overlay metrology: a review of the roadmap options (Invited Paper) [6922-01]**
M. Adel, D. Kandel, V. Levinski, J. Seligson, A. Kuniavsky, KLA-Tencor Corp. (Israel)
- 6922 03 **Overlay metrology at the crossroads (Invited Paper) [6922-02]**
N. P. Smith, Nanometrics Taiwan (Taiwan); L. A. Binns, Nanometrics, Ltd. (United Kingdom); A. Plambeck, K. Heidrich, Nanometrics, Inc. (USA)

SESSION 2 SOLUTIONS FOR TODAY

- 6922 04 **Production aspects of 45nm immersion lithography defect monitoring using laser DUV inspection methodology [6922-03]**
R. Kirsch, A. Martin, U. Okoroanyanwu, W. Grundkeb, U. Vogler, AMD (Germany); M. Beyer, Applied Materials Europe (Germany); E. Valfer, Applied Materials Israel (Israel); S. Weiher-Tellford, Applied Materials Europe (Germany); R. Perlovitch, N. Racah, Applied Materials Israel (Israel); P. Vanoppen, R. Moerman, ASML (Netherlands)
- 6922 06 **Immersion lithography bevel solutions [6922-158]**
L. Tedeschi, O. Tamada, M. Sanada, S. Yasuda, M. Asai, SOKUDO Co., Ltd. (Japan)
- 6922 07 **Versatile DUV scatterometer of the PTB and FEM based analysis for mask metrology [6922-05]**
M. Wurm, A. Diener, B. Bodermann, H. Gross, R. Model, Physikalisch-Technische Bundesanstalt (Germany); A. Rathsfeld, Weierstraß-Institut für Angewandte Analysis und Stochastik Mohrenstr (Germany)
- 6922 08 **Toward accurate feature shape metrology [6922-06]**
N. G. Orji, R. G. Dixson, National Institute of Standards and Technology (USA); B. D. Bunday, J. A. Allgair, International SEMATECH Manufacturing Initiative (USA)
- 6922 09 **Extracting dose and focus from critical dimension data: optimizing the inverse solution [6922-07]**
K. R. Lensing, J. B. Stirton, S. Chauhan, Advanced Micro Devices, Inc. (USA)

- 6922 0A **Challenges of implementing contour modeling in 32nm technology** [6922-08]
D. Fischer, G. Han, J. Oberschmidt, IBM Systems and Technology Group (USA); Y. W. Cheng, Chartered Semiconductor Manufacturing (USA); J. Y. Maeng, Samsung Electronics Co. (USA); C. Archie, W. Lu, IBM Systems and Technology Group (USA); C. Tabery, Advanced Micro Devices (USA)

SESSION 3 METHODS FOR TOMORROW

- 6922 0B **The potentials of helium ion microscopy for semiconductor process metrology** [6922-09]
M. T. Postek, A. E. Vladár, National Institute of Standards and Technology (USA)
- 6922 0C **Evaluating diffraction based overlay metrology for double patterning technologies** [6922-10]
C. S. Saravanan, Y. Liu, P. Dasari, Nanometrics, Inc. (USA); O. Kritsun, C. Volkman, A. Acheta, B. La Fontaine, Advanced Micro Devices, Inc. (USA)
- 6922 0D **Plasma cleaning of nanoparticles from EUV mask materials by electrostatics** [6922-12]
W. M. Lytle, R. Raju, H. Shin, C. Das, M. J. Neumann, D. N. Ruzic, Univ. of Illinois at Urbana-Champaign (USA)
- 6922 0E **Optical through-focus technique that differentiates small changes in line width, line height, and sidewall angle for CD, overlay, and defect metrology applications** [6922-13]
R. Attota, R. Silver, National Institute of Standards and Technology (USA); B. M. Barnes, KT Consulting, Inc. (USA)

SESSION 4 STANDARDS AND REFERENCE METROLOGY

- 6922 0F **Paving the way for multiple applications for the 3D-AFM technique in the semiconductor industry** [6922-14]
J. Foucher, CEA-LETI-MINATEC (France); E. Pargon, M. Martin, LTM (France); S. Reyne, CEA-LETI-MINATEC (France); C. Dupré, CEA-LETI-MINATEC (France) and IMEP-LAHC, INPG-MINATEC (France)
- 6922 0G **Controlled deposition of NIST-traceable nanoparticles as additional size standards for photomask applications** [6922-15]
J. Wang, D. Y. H. Pui, C. Qi, Univ. of Minnesota (USA); S.-J. Yook, Hanyang Univ. (South Korea); H. Fissan, Institute of Energy and Environmental Technology e.V. (Germany); E. Ultanir, T. Liang, Intel Corp. (USA)
- 6922 0H **Accurate and traceable dimensional metrology with a reference CD-SEM** [6922-16]
A. E. Vladár, J. S. Villarrubia, P. Cizmar, M. Oral, M. T. Postek, National Institute of Standards and Technology (USA)
- 6922 0I **Sub-nanometer pitch calibration and data quality evaluation methodology** [6922-17]
C.-M. Ke, Y. Wang, J. Huang, J. Hu, J. Huang, T.-S. Gau, B. J. Lin, Taiwan Semiconductor Manufacturing Co. (Taiwan)
- 6922 0J **A novel AFM method for sidewall measurement of high-aspect ratio patterns** [6922-18]
M. Watanabe, S. Baba, T. Nakata, Hitachi, Ltd. (Japan); T. Morimoto, S. Sekino, Hitachi Kenki FineTech Co., Ltd. (Japan)

- 6922 0K **TEM validation of CD AFM image reconstruction: part II** [6922-19]
G. A. Dahlen, Thorleaf Research, Inc. (USA); H.-C. Liu, M. Osborn, J. R. Osborne, Veeco Instruments, Inc. (USA); B. Tracy, A. del Rosario, Spansion, Inc. (USA)
- 6922 0L **Dimension controlled CNT probe of AFM metrology tool for 45-nm node and beyond**
[6922-20]
S. Sekino, T. Morimoto, T. Kurenuma, Hitachi Kenki FineTech Co., Ltd. (Japan); M. Hirooka, Hitachi, Ltd. (Japan); H. Tanaka, Hitachi Kyowa Engineering Co., Ltd. (Japan)

SESSION 5 OVERLAY I

- 6922 0M **Overlay metrology tool calibration using blossom** [6922-21]
L. A. Binns, N. P. Smith, P. Dasari, Nanometrics, Inc. (USA)
- 6922 0N **Using in-chip overlay metrology** [6922-22]
S. Girol-Gunia, B. Schulz, AMD Fab 36 LLC and Co. KG (Germany); N. Smith, L. Binns, Nanometrics, Inc. (United Kingdom)
- 6922 0O **Diffraction based overlay metrology: accuracy and performance on front end stack**
[6922-23]
P. Leray, S. Cheng, IMEC (Belgium); D. Kandel, M. Adel, A. Marchelli, I. Vakshtein, KLA-Tencor Corp. (Israel); M. Vasconi, STMicroelectronics (Italy); B. Salski, QWED (Poland)
- 6922 0P **Optimization of high order control including overlay, alignment, and sampling** [6922-106]
D. Choi, KLA-Tencor (South Korea); C. Lee, C. Bang, D. Cho, M. Gil, Hynix Semiconductor, Inc. (South Korea); P. Izikson, KLA-Tencor (Israel); S. Yoon, D. Lee, KLA-Tencor (South Korea)
- 6922 0Q **Overlay measurement based on dual-overlay grating image** [6922-24]
D.-M. Shyu, Y. Ku, S.-P. Dong, Industrial Technology Research Institute (Taiwan)

SESSION 6 SCATTEROMETRY I

- 6922 0R **Assessing scatterometry for measuring advanced spacer structures with embedded SiGe**
[6922-25]
M. Sendelbach, S. Zangoie, IBM Corp. (USA); A. Vaid, Advanced Micro Devices, Inc. (USA); P. Herrera, J. Leng, I. Kim, KLA-Tencor Corp. (USA)
- 6922 0S **Characterization of 32nm node BEOL grating structures using scatterometry** [6922-26]
S. Zangoie, M. Sendelbach, M. Angyal, C. Archie, IBM Microelectronics (USA); A. Vaid, I. Matthew, Advanced Micro Devices Inc. (USA); P. Herrera, KLA-Tencor Corp. (USA)
- 6922 0T **Advanced profile control and the impact of sidewall angle at gate etch for critical nodes**
[6922-27]
H. Lee, A. Ranjan, D. Prager, Tokyo Electron America, Inc. (USA); K. A. Bandy, E. Meyette, IBM Microelectronics (USA); R. Sundararajan, A. Viswanathan, A. Yamashita, M. Funk, Tokyo Electron America, Inc. (USA)

- 6922 0U **Scatterometry as technology enabler for embedded SiGe process** [6922-28]
A. Vaid, R. Pal, Advanced Micro Devices, Inc. (USA); M. Sendelbach, S. Zangooie, IBM Corp. (USA); K. Lensing, Advanced Micro Devices, Inc. (USA); C. Hartig, AMD Saxony Manufacturing GmbH (Germany)
- 6922 0V **Measurement of high-k and metal film thickness on FinFET sidewalls using scatterometry** [6922-29]
T. G. Dziura, KLA-Tencor (USA); B. Bunday, International SEMATECH Manufacturing Initiative (USA); C. Smith, M. M. Hussain, R. Harris, SEMATECH (USA); X. Zhang, KLA-Tencor (USA); J. M. Price, SEMATECH (USA)
- 6922 0W **Industrial characterization of scatterometry for advanced APC of 65 nm CMOS logic gate patterning** [6922-30]
K. Dabertrand, M. Touchet, STMicroelectronics (France); S. Kremer, KLA-Tencor (France); C. Chaton, CEA-LETI-Minatec (France); M. Gatefaït, E. Aparicio, STMicroelectronics (France); M. Polli, KLA-Tencor (France); J.-C. Royer, CEA-LETI-Minatec (France)

SESSION 7 PROCESS CONTROL

- 6922 0X **Impact of sampling on uncertainty: semiconductor dimensional metrology applications** [6922-31]
B. Bunday, ISMI, CD Metrology (USA); B. Rijpers, ASML, Research and Development, CD Metrology (Netherlands); B. Banke, C. Archie, IBM Microelectronics (USA); I. B. Peterson, Applied Materials, Inc. (USA); V. Ukrantsev, Veeco Instruments, Inc. (USA); T. Hingst, Qimonda Dresden (USA); M. Asano, Toshiba Corp. (Japan)
- 6922 0Y **CD uniformity control via real-time control of photoresist properties** [6922-32]
M. Chen, J. Fu, W. K. Ho, A. Tay, National Univ. of Singapore (Singapore)
- 6922 0Z **Process control for 45 nm CMOS logic gate patterning** [6922-33]
B. Le Gratiet, P. Gouraud, E. Aparicio, L. Babaud, K. Dabertrand, M. Touchet, STMicroelectronics (France); S. Kremer, KLA-Tencor (France); C. Chaton, CEA-Leti (France); F. Foussadier, F. Sundermann, J. Massin, J.-D. Chapon, M. Gatefaït, B. Minghetti, J. de-Caunes, D. Boutin, STMicroelectronics (France)
- 6922 10 **Improvement of gate CD uniformity for 55 nm node logic devices** [6922-34]
T. Murakami, T. Nakata, K. Taniguchi, T. Uchiyama, NEC Electronics Corp. (Japan); M. Jyousaka, M. Tadokoro, Tokyo Electron Kyushu, Ltd. (Japan); Y. Konishi, Tokyo Electron Software Technologies, Ltd. (Japan)
- 6922 11 **Metrology characterization for self-aligned double patterning** [6922-35]
A. Berger, S. Latinsky, M. Bar-Zvi, R. Peltinov, Applied Materials (Israel); J. Shu, C. Ngai, J. Yu, H. Dai, Applied Materials (USA)
- 6922 12 **Focus and dose control to actual process wafer** [6922-36]
H. Ina, K. Sentoku, Canon, Inc. (Japan)

SESSION 8 INSPECTION AND DEFECT	
6922 13	Defect criticality index (DCI): a new methodology to significantly improve DOI sampling rate in a 45nm production environment [6922-37] Y. Sato, Y. Yamada, Y. Kaga, Y. Yamazaki, Toshiba Corp. (Japan); M. Aoki, D. Tsui, C. Young, E. Chang, KLA-Tencor Corp. (USA)
6922 14	Lot acceptance sampling inspection plan for non-normal CD distribution [6922-38] T. Ikeda, M. Asano, Toshiba Corp. (Japan)
6922 15	Improvements on the simulation of microscopic images for the defect detection of nanostructures [6922-39] S. Rafler, T. Schuster, K. Frenner, W. Osten, Institut für Technische Optik (Germany); U. Seifert, Qimonda Dresden GmbH and Co. OHG (Germany)
6922 16	Defect inspection using a high-resolution pattern image obtained from multiple low-resolution images of the same pattern on an observed noisy SEM image [6922-40] M. Takashima, Y. Midoh, K. Nakamae, Osaka Univ. (Japan)
6922 17	Contamination specification for dimensional metrology SEMs [6922-41] A. E. Vladár, K. P. Purushotham, M. T. Postek, National Institute of Standards and Technology (USA)
6922 18	In-line inspection resistance mapping using quantitative measurement of voltage contrast in SEM images [6922-42] M. Matsui, Y. Anan, T. Odaka, Hitachi, Ltd. (Japan); H. Nagaishi, K. Sakurai, Renesas Technology Corp. (Japan)
SESSION 9 CDSEM I	
6922 19	Experiment and simulation of charging effects in SEM [6922-43] S. Babin, S. Borisov, aBeam Technologies, Inc. (USA); Y. Miyano, H. Abe, M. Kadokawa, A. Hamaguchi, Y. Yamazaki, Toshiba Corp. (Japan)
6922 1A	Characterization of CD-SEM metrology for iArF photoresist materials [6922-44] B. Bunday, A. Cordes, International SEMATECH Manufacturing Initiative (USA); N. G. Orji, National Institute of Standards and Technology (USA); E. Piscani, D. Cochran, J. Byers, SEMATECH, Inc. (USA); J. Allgair, International SEMATECH Manufacturing Initiative (USA); B. J. Rice, SEMATECH, Inc. (USA); Y. Avitan, R. Peltinov, M. Bar-zvi, O. Adan, Applied Materials (Israel)
6922 1B	Advanced CD-SEM metrology to improve total process control performance for hyper-NA lithography [6922-45] M. Osaki, Hitachi, Ltd. (Japan) and IMEC vzw (Belgium); M. Tanaka, C. Shishido, Hitachi, Ltd. (Japan); T. Ishimoto, Hitachi High-Technologies Corp. (Belgium) and IMEC vzw (Belgium); N. Hasegawa, Hitachi High-Technologies Corp. (Japan); K. Sekiguchi, Hitachi High-Technologies Europe GmbH (Germany) and IMEC vzw (Belgium); K. Watanabe, Hitachi High-Technologies Corp. (Japan); S. Cheng, D. Laidler, M. Ercken, E. Altamirano, IMEC (Belgium)

- 6922 1C **CD-SEM contour-based process monitoring in DRAM production environment** [6922-47]
U. Kramer, D. Jackisch, R. Wildfeuer, S. Fuchs, F. Jauzion-Graverolle, Qimonda Dresden GmbH and Co. OHG (Germany); G. Ben-Nahumb, O. Menadeva, S. Ventola, Applied Materials, Inc. (Israel)

SESSION 10 OVERLAY II

- 6922 1D **Accurate in-resolution level overlay metrology for multipatterning lithography techniques** [6922-48]
I. England, R. Piech, C. Masia, Applied Materials Europe (Netherlands); N. Hillel, L. Gershtein, D. Sofer, R. Peltinov, O. Adan, Applied Materials (Israel)
- 6922 1E **Sources of overlay error in double patterning integration schemes** [6922-49]
D. Laidler, P. Leray, K. D'havé, S. Cheng, IMEC (Belgium)
- 6922 1F **Correlating overlay metrology precision to interlayer dielectric film properties** [6922-52]
K. R. Paserba, Seagate Technology LLC (USA)
- 6922 1G **Overlay improvement by zone alignment strategy** [6922-53]
C.-Y. Huang, A.-Y. Lee, C.-L. Shih, Nanya Technology Corp. (Taiwan); R. Yang, M. Yuan, H. Chen, R. Chang, Inotera Memories, Inc. (Taiwan)

SESSION 11 CD FOR DEVELOPMENT AND OPC

- 6922 1H **Challenges of OPC model calibration from SEM contours** [6922-54]
Y. Granik, I. Kusnadi, Mentor Graphics Corp. (USA)
- 6922 1I **Empirical data validation for model building** [6922-55]
A. Kazarian, Synopsys, Inc. (USA)
- 6922 1J **Automated creation of production metrology recipes based on design information** [6922-56]
J. P. Cain, M. Threefoot, K. Shah, Advanced Micro Devices, Inc. (USA); B. Schulz, S. Girol-Gunia, J.-T. Hoeft, AMD Fab36 LLC and Co. KG (Germany)
- 6922 1K **Impact of assistance feature to pattern profile for isolated feature in sub-65 nm node** [6922-57]
M. Kim, Y.-J. Yun, E. Jeong, K. Choi, J. Kim, J. Han, DongbuHitek Co., Ltd. (South Korea)
- 6922 1L **Accurate device simulations through CD-SEM-based edge-contour extraction** [6922-95]
E. Shauly, Tower Semiconductors (Israel); O. Menadeva, Applied Materials, Inc. (Israel); R. Drori, M. Cohen-Yasour, I. Rotstein, Tower Semiconductors (Israel); R. Peltinov, A. Bartov, S. Latinski, A. Siany, M. Geshesl, Applied Materials, Inc. (Israel)

SESSION 12 SCATTEROMETRY II

- 6922 1M **Angle resolved optical metrology** [6922-59]
R. M. Silver, National Institute of Standards and Technology (USA); B. M. Barnes, KT Consulting, Inc. (USA); A. Heckert, R. Attota, R. Dixson, National Institute of Standards and Technology (USA); J. Jun, KT Consulting, Inc. (USA)
- 6922 1N **Opportunities and challenges for optical CD metrology in double patterning process control** [6922-60]
D. C. Wack, J. Hench, L. Poslavsky, J. Fielden, V. Zhuang, W. Mieher, T. Dziura, KLA-Tencor (USA)
- 6922 1O **Forward solve algorithms for optical critical dimension metrology** [6922-61]
P. L. Jiang, H. Chu, Tokyo Electron, Ltd. (USA); J. Hench, D. Wack, KLA-Tencor (USA)
- 6922 1P **Comparison of spectroscopic Mueller polarimetry, standard scatterometry, and real space imaging techniques (SEM and 3D-AFM) for dimensional characterization of periodic structures** [6922-62]
A. De Martino, M. Foldyna, T. Novikova, Lab. de Physique des Interfaces et des Couches Minces, Ecole Polytechnique (France); D. Cattelan, Jobin Yvon HORIBA (France); P. Baritault, C. Licitra, J. Hazart, J. Foucher, F. Bogaert, CEA-LETI Minatec (France)

SESSION 13 CDSEM II

- 6922 1R **Physical matching of CD-SEM: noise analysis and verification in FAB environment** [6922-65]
U. Kramer, A. Navarra, G. Fleischer, J. Kaiser, F. Voss, Qimonda Dresden GmbH and Co. OHG (Germany); G. Zuckerman, R. Kris, I. Ben-Dayan, E. Sommer, A. Len, S. Dror, Applied Materials, Inc. (Israel); D. Schöne, S. Ventola, Applied Materials, Inc. (Germany)
- 6922 1S **AWV: high-throughput cross-array cross-wafer variation mapping** [6922-66]
J.-H. Yeo, B.-H. Lee, T.-Y. Lee, Samsung Electronics Co., Ltd. (South Korea); G. Greenberg, D. Meshulach, E. Ravid, S. Levi, K. Kan, S. Shabtay, Y. Cohen, O. Rotlevy, Applied Materials Israel (Israel)
- 6922 1T **CD bias reduction in CD-SEM linewidth measurements for advanced lithography** [6922-67]
M. Tanaka, Hitachi, Ltd. (Japan); J. Meessen, ASML (Netherlands); C. Shishido, Hitachi, Ltd. (Japan); K. Watanabe, Hitachi High-Technologies Corp. (Japan); I. Minnaert-Janssen, P. Vanoppen, ASML (Netherlands)
- 6922 1U **Automatic CD-SEM offline recipe creation in a high volume production fab** [6922-69]
S. Girol-Gunia, S. Roling, AMD Fab36 LLC and Co. KG (Germany); O. Menadeva, D. Levitzky, A. Costa, D. Fischer, Applied Materials, Inc. (Israel)
- 6922 1V **Automated CD-SEM metrology for efficient TD and HVM** [6922-70]
A. Starikov, S. P. Mulapudi, Intel Corp. (USA)

Part Two

SESSION 14 NOVEL METHODS AND APPLICATIONS

- 6922 1W **Modeling for metrology with a helium beam** [6922-71]
R. Ramachandra, Univ. of Tennessee (USA); B. J. Griffin, Univ. of Western Australia (Australia) and Oak Ridge National Lab. (USA); D. C. Joy, Univ. of Tennessee (USA) and Oak Ridge National Lab. (USA)
- 6922 1X **Novel CD inspection technology leveraging a form birefringence in a Fourier space** [6922-72]
A. Kawai, D. Mochida, Nikon Corp. (Japan); K. Yoshino, Y. Yamazaki, Toshiba Corp. (Japan)
- 6922 1Y **Experimental quantification of reticle electrostatic damage below the threshold for ESD** [6922-73]
G. C. Rider, Microtome, Inc. (USA); T. S. Kalkur, Univ. of Colorado at Colorado Springs (USA)
- 6922 1Z **Linewidth roughness and cross-sectional measurements of sub-50 nm structures with CD-SAXS and CD-SEM** [6922-74]
C. Wang, National Institute of Standards and Technology (USA); K.-W. Choi, Intel Corp. (USA); R. L. Jones, C. Soles, E. K. Lin, W. Wu, National Institute of Standards and Technology (USA); J. S. Clarke, Intel Corp. (USA); J. S. Villarrubia, National Institute of Standards and Technology (USA); B. Bunday, International SEMATECH Manufacturing Initiative (USA)

SESSION 15 LINE-EDGE ROUGHNESS

- 6922 20 **A novel method for pushing the limits of line edge roughness detection by scatterometry** [6922-75]
Y. Cohen, Nova Measuring Instruments Ltd. (Israel); B. Yaakovovitz, Y. Tsur, Technion-Israel Institute of Technology (Israel); D. Scheiner, Nova measuring Instruments, Ltd. (Israel)
- 6922 21 **Influence of image processing on line-edge roughness in CD-SEM measurement** [6922-76]
A. Yamaguchi, J. Yamamoto, Hitachi, Ltd. (Japan)
- 6922 22 **Practical and bias-free LWR measurement by CDSEM** [6922-77]
S.-B. Wang, Y. H. Chiu, H. J. Tao, Y. J. Mii, Taiwan Semiconductor Manufacturing Co., Ltd. (Taiwan)
- 6922 23 **Fractal dimension of line width roughness and its effects on transistor performance** [6922-156]
V. Constantoudis, E. Gogolides, Institute of Microelectronics (Greece)

POSTER SESSION

- 6922 24 **Exploring the limitations of x-ray reflectivity as a critical dimension pattern shape metrology** [6922-11]
H.-J. Lee, S. Kim, C. L. Soles, E. K. Lin, W. Wu, National Institute of Standards and Technology (USA)

- 6922 25 **Probe-pattern grating focus monitor through scatterometry calibration** [6922-63]
J. Xue, C. J. Spanos, A. R. Neureuther, Univ. of California, Berkeley (USA)
- 6922 26 **An objective image focus for CD-SEM** [6922-68]
H. Zhang, C. Gould, B. Roberts, M. McQuillan, Qimonda North America (USA)
- 6922 27 **Ellipsometric inspection of the inner surface of pellicle-covered masks** [6922-78]
S. Lee, Hanyang Univ. (South Korea); C. Song, Hanyang Univ. (South Korea) and Samsung Electronics Co. (South Korea); J. Rhim, H. Lee, J. Kyoung, Hanyang Univ. (South Korea); S. Chin, T. Ahn, Samsung Electronics Co. (South Korea); I. An, Hanyang Univ. (South Korea)
- 6922 28 **Optics characterization with compact EUV spectrophotometer** [6922-79]
H. Blaschke, I. Balasa, L. Koch, K. Starke, D. Ristau, Laser Zentrum Hannover e.V. (Germany); C. Wies, R. Lebert, AIXUV Aachen (Germany); A. Bayer, F. Barkusky, K. Mann, Laser-Lab. Göttingen e.V. (Germany)
- 6922 29 **Verification of optics for the die-to-wafer-like image mask inspection** [6922-80]
A. Takada, T. Tojo, Topcon Corp. (Japan); M. Shibuya, Tokyo Polytechnic Univ. (Japan)
- 6922 2A **Phase metrology on 45-nm node phase-shift mask structures** [6922-81]
K. M. Lee, M. Tavassoli, Intel Mask Operation (USA); U. Buttgereit, D. Seidel, R. Birkner, S. Perlitz, Carl Zeiss SMS GmbH (Germany)
- 6922 2B **A new high-resolution photomask inspection system for contamination detection** [6922-82]
B. Mu, A. Dayal, L.-H. Yiin, J. Zhu, J. Miller, G. Inderhees, KLA-Tencor Corp. (USA)
- 6922 2C **Systematic defect inspection and verification for distributions of critical dimension in OPC models utilizing design based metrology tool** [6922-83]
J.-G. Park, S. Lee, Y.-S. Kang, Y.-K. Park, Samsung Electronics Co. Ltd. (South Korea); T. Kitamura, T. Hasebe, S. Nakazawa, NanoGeometry Research Inc. (Japan)
- 6922 2D **Advanced method to monitor design-process marginality for 65nm node and beyond** [6922-84]
C. Huang, Advanced Metrology Dept. CRD Advanced Modules Div. (USA); C. Young, KLA-Tencor Corp. (USA); H. Liu, S. F. Tzou, Advanced Metrology Dept. CRD Advanced Modules Div. (USA); D. Tsui, E. Chang, KLA-Tencor Corp. (USA)
- 6922 2E **CD-SAXS measurements using laboratory-based and synchrotron-based instruments** [6922-85]
C. Wang, National Institute of Standards and Technology (USA); K.-W. Choi, Intel Corp. (USA); W.-E. Fu, D. L. Ho, R. L. Jones, C. Soles, E. K. Lin, W. Wu, National Institute of Standards and Technology (USA); J. S. Clarke, Intel Corp. (USA); B. Bunday, International SEMATECH Manufacturing Initiative (USA)
- 6922 2F **A novel methodology for model-based OPC verification** [6922-86]
T. Huang, C. Liao, Nanya Technology Corp. (Taiwan); R. Chou, H.-Y. Liao, J. Schacht, Mentor Graphics Corp. (Taiwan)
- 6922 2H **Effect of setpoint on CD measurement in CD-AFM: plausibility study** [6922-88]
B. C. Park, J. Choi, S. J. Ahn, Korea Research Institute of Standards and Science (South Korea); M. Shin, D. Ihm, B. Lee, Samsung Electronics Co., Ltd. (South Korea)

- 6922 2J **Recent CD AFM probe developments for sub-45 nm technology nodes** [6922-91]
H.-C. Liu, J. R. Osborne, G. A. Dahlen, Veeco Instruments, Inc. (USA); J. Greschner, T. Bayer, S. Kalt, G. Fritz, Team Nanotec GmbH (Germany)
- 6922 2K **Electron-beam-patterning simulation and metrology of complex layouts on Si/Mo multilayer substrates** [6922-92]
G. P. Patsis, D. Drygiannakis, Institute of Microelectronics (Greece); N. Tsikrikas, Institute of Microelectronics (Greece) and National Technical Univ. of Athens (Greece); I. Raptis, E. Gogolides, Institute of Microelectronics (Greece)
- 6922 2L **Application of model-based library approach to Si₃N₄ hardmask measurements** [6922-93]
M. Tanaka, C. Shishido, W. Nagatomo, Hitachi, Ltd. (Japan); K. Watanabe, Hitachi High-Technologies Corp. (Japan)
- 6922 2M **Calibration of CD-SEM: moving from relative to absolute measurements** [6922-94]
S. Babin, S. Borisov, A. Ivanchikov, I. Ruzavin, Abeam Technologies, Inc. (USA)
- 6922 2N **Automated metrology for SEM calibration and CD line measurements using image analysis and SEM modeling methods** [6922-96]
V. Khvatkov, V. Alievski, R. Kadushnikov, Smart Imaging Technologies (USA); S. Babin, aBeam Technologies (USA)
- 6922 2O **Further study on the verification of CD-SEM based monitoring for hyper NA lithography** [6922-97]
T. Ishimoto, Hitachi High-Technologies Corp. (Japan); M. Osaki, Hitachi, Ltd. (Japan); K. Sekiguchi, Hitachi High-Technologies Europe GmbH (Germany); N. Hasegawa, K. Watanabe, Hitachi High-Technologies Corp. (Japan); D. Laidler, S. Cheng, IMEC vzw (Belgium)
- 6922 2P **MuGFET observation and CD measurement by using CD-SEM** [6922-98]
T. Maeda, Hitachi High-Technologies Corp. (Japan); M. Tanaka, Hitachi, Ltd. (Japan); M. Isawa, K. Watanabe, N. Hasegawa, Hitachi High-Technologies Corp. (Japan); K. Sekiguchi, Hitachi High-Technologies Europe GmbH (Germany); R. Rooyackers, N. Collaert, T. Vandeweyer, IMEC vzw (Belgium)
- 6922 2Q **High order correction and sampling strategy for 45nm immersion lithography overlay control** [6922-99]
B. Y. Hsueh, G. K. C. Huang, C.-C. Yu, J. K. C. Hsu, United Microelectronics Corp. (Taiwan); C.-C. K. Huang, C.-J. Huang, D. Tien, KLA-Tencor Corp. (USA)
- 6922 2R **Improve overlay control and scanner utilization through high order corrections** [6922-100]
H. M. Lin, B. Lin, J. Wu, S. Chiu, Powerchip Semiconductor Corp. (Taiwan); C.-C. K. Huang, J. Manka, D. Goh, H. Huang, D. Tien, KLA-Tencor Corp. (USA)
- 6922 2S **Overlay control using scatterometry based metrology (SCOM) in production environment** [6922-101]
B. Dinu, KLA-Tencor Corp. (Israel); S. Fuchs, U. Kramer, M. Kubis, Qimonda Dresden GmbH and Co. OHG (Germany); A. Marchelli, KLA-Tencor Corp. (Israel); A. Navarra, Qimonda Dresden GmbH and Co. OHG (Germany); C. Sparka, A. Widmann, KLA-Tencor Corp. (Israel)

- 6922 2T **Alignment system and process optimization for improvement of double patterning overlay** [6922-103]
 W. Ma, J. Kang, C. Lim, H. Kim, S. Moon, Hynix Semiconductor, Inc. (South Korea);
 S. Lalbahadoersing, S. Oh, ASML (Netherlands)
- 6922 2U **Sampling for advanced overlay process control** [6922-105]
 D. Choi, KLA-Tencor Korea Co., Ltd. (South Korea); P. Izikson, KLA-Tencor Corp. (Israel);
 D. Sutherland, K. Sherman, J. Manka, J. C. Robinson, KLA-Tencor Corp. (USA)
- 6922 2V **A system to optimize mix-and-match overlay in lithography** [6922-107]
 S. Wakamoto, Y. Ishii, K. Yasukawa, Nikon Corp. (Japan); S. Maejima, Renesas Technology Corp. (Japan); A. Kato, KLA-Tencor Japan, Ltd. (Japan); J. C. Robinson, KLA-Tencor Corp. (USA); D.-S. Choi, KLA-Tencor Korea Co., Ltd. (South Korea)
- 6922 2W **Diffraction based overlay metrology for α -carbon applications** [6922-108]
 C. S. Saravanan, A. Tan, P. Dasari, G. Goelzer, N. Smith, Nanometrics Inc. (USA); S.-H. Woo, J. H. Shin, H. J. Kang, H. C. Kim, Samsung Electronics Co., Ltd. (South Korea)
- 6922 2X **Film stacking architecture for immersion lithography process** [6922-109]
 T. Goto, M. Sanada, T. Miyagi, K. Shigemori, M. Kanaoka, S. Yasuda, O. Tamada, M. Asai, SOKUDO Co., Ltd. (Japan)
- 6922 2Y **Controlling macro and micro surface topography for a 45nm copper CMP process using a high resolution profiler** [6922-111]
 T. Ortleb, G. Marxsen, J. Heinrich, AMD LLC and Co. KG (Germany); J. Reichert, R. Haupt, P. Yam, KLA-Tencor (USA)
- 6922 2Z **Effects produced by CDU improvement of resist pattern with PEB temperature control for wiring resistance variation reduction** [6922-112]
 M. Tadokoro, S. Shinozuka, Tokyo Electron Kyushu, Ltd. (Japan); K. Ogata, T. Morimoto, Tokyo Electron, Ltd. (Japan)
- 6922 30 **Rationalizing the mechanism of HMDS degradation in air and effective control of the reaction byproducts** [6922-113]
 K. Seguin, A. J. Dallas, G. Weineck, Donaldson Co., Inc. (USA)
- 6922 31 **Stress measurement system for process control** [6922-114]
 K. Akashika, M. Horie, Dainippon Screen Manufacturing Co., Ltd. (Japan)
- 6922 34 **CDU improvement technology of etching pattern using photo lithography** [6922-117]
 M. Tadokoro, S. Shinozuka, M. Jyousaka, Tokyo Electron Kyushu, Ltd. (Japan); K. Ogata, T. Morimoto, Tokyo Electron, Ltd. (Japan); Y. Konishi, Tokyo Electron Software Technologies, Ltd. (Japan)
- 6922 35 **Film thickness measurement tool with a stress measurement function** [6922-118]
 M. Horie, K. Akashika, S. Shiota, S. Yamaguchi, K. Yamano, Dainippon Screen Manufacturing Co., Ltd. (Japan)

- 6922 37 **In-situ real-time temperature control of baking systems in lithography** [6922-120]
Y. Wang, National Univ. of Singapore (Singapore); H.-T. Chua, The Univ. of Western Australia (Australia); A. Tay, National Univ. of Singapore (Singapore)
- 6922 38 **Dimensionality reduction methods in virtual metrology** [6922-121]
D. Zeng, Y. Tan, C. J. Spanos, Univ. of California, Berkeley (USA)
- 6922 39 **Wide applications of design based metrology with tool integration** [6922-123]
H. Yang, J. Kim, A. Jung, T. Lee, D. Yim, J. Kim, Hynix Semiconductor, Inc. (South Korea); T. Hasebe, M. Yamamoto, NanoGeometry Research, Inc. (Japan)
- 6922 3A **Wafer edge polishing process for defect reduction during immersion lithography** [6922-125]
M. Okazaki, Applied Materials (USA); R. Maas, ASML Netherlands B.V. (Netherlands); S.-H. Ko, Y. Chen, P. Miller, M. Thothadri, M. Dutta, C.-P. Chang, A. Anapolsky, C. Lazik, Y. Uritsky, M. Seamons, D. Padhi, W. Yeh, Applied Materials (USA); S. Sinkwitz, ASML Netherlands B.V. (Netherlands); C. Ngai, Applied Materials (USA)
- 6922 3B **High throughput wafer defect monitor for integrated metrology applications in photolithography** [6922-126]
N. Rao, P. Kinney, A. Gupta, Real Time Metrology, Inc. (USA)
- 6922 3D **UV-reflectometry for fast trench-depth measurement** [6922-128]
M. Horie, S. Shiota, S. Yamaguchi, K. Yamano, M. Kobayashi, Dainippon Screen Manufacturing Co., Ltd. (Japan)
- 6922 3E **Study of ADI (After Develop Inspection) on photo resist wafers using electron beam (III): novel method for ADI on metal hard mask by penetration contrast** [6922-129]
T. Hayashi, M. Saito, K. Fujihara, Tokyo Electron, Ltd. (Japan); J. Jau, Hermes Microvision, Inc. (USA)
- 6922 3G **Improving dry etch control for contact plugs in advanced DRAM manufacturing** [6922-131]
T. Bao, Veeco Instruments, Inc. (USA); Y. Bar, Micron Technology, Inc. (USA); D. Fong, Veeco Instruments, Inc. (USA); M. Godbole, Micron Technology, Inc. (USA)
- 6922 3H **In-line focus-dose monitoring for hyper NA imaging** [6922-132]
S. Loi, A. Fasciszewski Zeballos, U. Iessi, STMicroelectronics (Italy); J. Robinson, KLA-Tencor Corp. (USA); P. Izikson, KLA-Tencor (Israel); A. Mani, M. Polli, KLA-Tencor (Italy)
- 6922 3J **Picometer-scale accuracy in pitch metrology by optical diffraction and atomic force microscopy** [6922-134]
D. A. Chernoff, Advanced Surface Microscopy, Inc. (USA); E. Buhr, Physikalisch-Technische Bundesanstalt (Germany); D. L. Burkhead, Advanced Surface Microscopy, Inc. (USA); A. Diener, Physikalisch-Technische Bundesanstalt (Germany)
- 6922 3K **Development of back-end-of-the-line applications using optical digital profilometry (ODP)** [6922-135]
J.-J. Huang, J. H. Yeh, United Microelectronics Corp. (Taiwan); Y. Luo, L. Wu, Y. Wen, Timbre Technologies (USA)
- 6922 3L **Scatterometry based overlay metrology** [6922-136]
T. Matsumoto, H. Ina, K. Sentoku, S. Oishi, Canon, Inc. (Japan)

- 6922 3M **Spectroscopic ellipsometer for ultra thin film** [6922-137]
 K. Akashika, S. Shiota, S. Yamaguchi, M. Horie, M. Kobayashi, Dainippon Screen Manufacturing Co., Ltd. (Japan)
- 6922 3N **Characterization of sub-50-nm line array structures with angle-resolved multiple wavelength scatterometry** [6922-139]
 M. Kotelyanskii, F. Shen, G. Jiang, Rudolph Technologies, Inc. (USA); B. Bunday, ISMI (USA)
- 6922 3O **Sensitivity and performance estimates for the multiple wavelength multiple incidence angle ellipsometry for OCD applications** [6922-140]
 M. Kotelyanskii, G. Jiang, Rudolph Technologies, Inc. (USA)
- 6922 3P **Modeling the effect of finite size gratings on scatterometry measurements** [6922-142]
 E. Kenyon, M. W. Cresswell, National Institute of Standards and Technology (USA); H. J. Patrick, National Institute of Standards and Technology (USA) and KT Consulting, Inc. (USA); T. A. Germer, National Institute of Standards and Technology (USA)
- 6922 3Q **Characterization of the poly gate ACI structure with laser based angle resolved multiple wavelength scatterometry** [6922-143]
 G. Jiang, M. Kotelyanskii, F. Shen, Rudolph Technologies, Inc. (USA)
- 6922 3R **Low-k n&k variation impact on CD accuracy of scatterometry** [6922-145]
 Y. Chen, Timbre Technologies, Inc. (USA); M. Yamamoto, Tokyo Electron, Ltd. (Japan); D. Likhachev, G. He, Timbre Technologies, Inc. (USA); A. Sonoda, Tokyo Electron, Ltd. (Japan); V. Vuong, Timbre Technologies, Inc. (USA)
- 6922 3S **Implementation of spectroscopic critical dimension (SCD) for leveling inline monitor of ASML 193nm scanner** [6922-146]
 W. K. Lin, M. Yeh, United Microelectronics Corp. (Taiwan)
- 6922 3T **3D semiconductor grooves measurement simulations (scatterometry) using nonstandard FDTD methods** [6922-147]
 H. Shirasaki, Tamagawa Univ. (Japan)
- 6922 3U **Novel approach for immersion lithography defectivity control to increase productivity** [6922-148]
 I. Englard, Applied Materials Europe (Netherlands); R. Stegen, P. Vanoppen, I. Minnaert-Janssen, T. der Kinderen, E. van Brederode, F. Duray, J. Linders, D. Ovchinnikov, ASML (Netherlands); R. Piech, C. Masia, Applied Materials Europe (Netherlands); N. Hillel, E. Ravid, O. Rotlevi, A. Wilde, S. Shabtay, Z. Telor, Applied Materials Israel (Israel); R. Schreutelkamp, Applied Materials Europe (Netherlands)
- 6922 3V **Traceable calibration of AFM step height measurements for integrated circuit manufacturing** [6922-149]
 J. Robert, B. Banke, IBM Microelectronics (USA); R. Dixson, National Institute of Standards and Technology (USA); C. Strocchia-Rivera, IBM Microelectronics (USA)
- 6922 3X **22 nm node contact hole formation in extreme ultra-violet lithography** [6922-151]
 E.-J. Kim, Hanyang Univ. (South Korea); K.-H. Kim, H.-R. Park, J.-Y. Yeo, J.-S. Kim, Seoul National Univ. (South Korea); H.-K. Oh, Hanyang Univ. (South Korea)

- 6922 3Y **Advanced lithography parameters extraction by using scatterometry system: part II**
[6922-152]
W. Zhou, M. Hsieh, H. Koh, M. Zhou, Chartered Semiconductor Manufacturing, Ltd.
(Singapore)
- 6922 42 **Compensating for SSIS sizing/classification error in a defect review SEM world** [6922-157]
D. Ruprecht, MEMC Electronic Materials, Inc. (USA); S. McGarvey, Hitachi High
Technologies America, Inc. (USA)

Author Index

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1 Invited Session

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Inc. (USA)

Christopher J. Raymond, Nanometrics Inc. (USA)

2 Solutions for Today

Brian M. Trafas, KLA-Tencor Corporation (USA)

Alexander Starikov, Intel Corporation (USA)

- 3 Methods for Tomorrow
Christopher J. Raymond, Nanometrics, Inc. (USA)
Daniel J. C. Herr, Semiconductor Research Corporation (USA)
- 4 Standards and Reference Metrology
Vladimir A. Ukrainsev, Veeco Instruments, Inc. (USA)
David C. Joy, The University of Tennessee (USA)
- 5 Overlay I
Brian M. Trafas, KLA-Tencor Corporation (USA)
Daniel J. C. Herr, Semiconductor Research Corporation (USA)
- 6 Scatterometry I
Christopher J. Raymond, Nanometrics, Inc. (USA)
Richard M. Silver, National Institute of Standards and Technology (USA)
- 7 Process Control
Jason P. Cain, Advanced Micro Devices, Inc. (USA)
Alexander Starikov, Intel Corporation (USA)
- 8 Inspection and Defect
Byoung-Ho Lee, SAMSUNG Electronics Company, Ltd. (South Korea)
Martha I. Sanchez, IBM Almaden Research Center (USA)
- 9 CDSEM I
John A. Allgair, SEMATECH, Inc. (USA) and Advanced Micro Devices, Inc. (USA)
Ofer Adan, Applied Materials (Israel)
- 10 Overlay II
David C. Joy, The University of Tennessee (USA)
- 11 CD for Development and OPC
Ofer Adan, Applied Materials (Israel)
Christopher J. Raymond, Nanometrics, Inc. (USA)
- 12 Scatterometry II
Christopher J. Raymond, Nanometrics, Inc. (USA)
Alexander Starikov, Intel Corporation (USA)
- 13 CDSEM II
Martha I. Sanchez, IBM Almaden Research Center (USA)
John A. Allgair, SEMATECH, Inc. (USA) and Advanced Micro Devices, Inc. (USA)

- 14 Novel Methods and Applications
Richard M. Silver, National Institute of Standards and Technology
(USA)
Jason P. Cain, Advanced Micro Devices, Inc. (USA)
- 15 Line-Edge Roughness
Martha I. Sanchez, IBM Almaden Research Center (USA)
Ofer Adan, Applied Materials (Israel)

